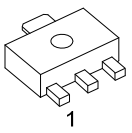
2SC3357

NPN SILICON TRANSISTOR

NPN EPITAXIAL SILICON RF TRANSISTOR
HIGH-FREQUENCY LOW-NOISE AMPLIFICATION POWER MINI MOLD



SOT-89

■ DESCRIPTION

The UTC **2SC3357** is an NPN silicon epitaxial transistor designed for low noise amplifier at VHF, UHF and CATV band.

It has large dynamic range and good current characteristic.

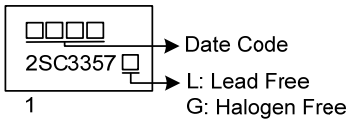
■ ORDERING INFORMATION

Order Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2SC3357L-xx-AB3-R	2SC3357G-xx-AB3-R	SOT-89	B	C	E	Tape Reel

Note: Pin Assignment: B: Base C: Collector E: Emitter

2SC3357G-xx-AB3-R (1)Packing Type (2)Package Type (3)Rank (4)Green Package	(1) R: Tape Reel (2) AB3: SOT-89 (3) xx: refer to Classification of h_{FE} (4) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUATE MAXIUM RATINGS (T_A= 25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector to Base Voltage	V_{CBO}	20	V
Collector to Emitter Voltage	V_{CEO}	12	V
Emitter to Base Voltage	V_{EBO}	3	V
Collector Current	I_C	100	mA
Collector Dissipation	P_C	1.2	W
Junction Temperature	T_J	+150	°C
Storage Temperature	T_{STG}	-40 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Cut-off Current	I_{CBO}	V_{CE}=10V, I_E=0			1	μA
Emitter Cutoff Current	I_{EBO}	V_{CE}=1V, I_C=0			1	μA
DC Current Gain	h_{FE}	V_{CE}=10V, I_C=20mA	50		300	
Transition Frequency	f_T	V_{CE}=10V, I_C=20mA		6.5		GHz
Feedback Capacitance	C_{re}	V_{CE}=10V, I_E=0, f=1MHz			10	pF

Note: Pulsed: $P_W \leq 350\mu s$, Duty Cycle ≤ 2%.

■ CLASSIFICATION OF h_{FE}

RANK	RH	RF	RE
RANGE	50 ~ 100	80 ~ 160	125 ~ 250

■ TYPICAL CHARACTERISTICS